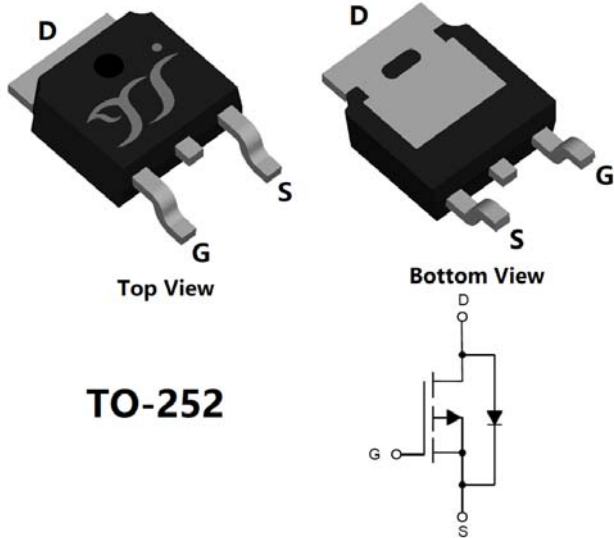


P-Channel Enhancement Mode Field Effect Transistor



TO-252

Product Summary

- V_{DS} -100V
- I_D -18A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) < 110 m Ω
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) < 120 m Ω
- 100% UIS Tested
- 100% ∇V_{DS} Tested

General Description

- Split gate trench MOSFET technology
- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Part no. with suffix "Q" means AEC-Q101 qualified

Applications

- Power management
- Portable equipment

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	-100	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_c=25^\circ\text{C}$	I_D	-18	A
	$T_c=100^\circ\text{C}$		-12	
Pulsed Drain Current ^A		I_{DM}	-72	A
Avalanche energy ^B		EAS	36	mJ
Total Power Dissipation ^C	$T_c=25^\circ\text{C}$	P_D	72	W
	$T_c=100^\circ\text{C}$		29	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	40	50	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1.35	1.7	

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJD18GP10AQ	F1	YJD18GP10A	2500	2500	25000	13" reel



YJD18GP10AQ

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =-250μA	-100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V	-	-	-1	μA
		V _{DS} =-100V, V _{GS} =0V, T _J =150°C	-	-	-100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =-250μA	-1.0	-1.8	-2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-10A	-	83	110	mΩ
		V _{GS} =-4.5V, I _D =-5A	-	95	120	
Diode Forward Voltage	V _{SD}	I _S =-10A, V _{GS} =0V	-	-	-1.3	V
Gate resistance	R _G	f=1MHz, Open drain	-	10	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	-18	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =-50V, V _{GS} =0V, f=1MHz	-	1051	-	pF
Output Capacitance	C _{oss}		-	119	-	
Reverse Transfer Capacitance	C _{rss}		-	25	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =-10V, V _{DS} =-50V, I _D =-5A	-	20.1	-	nC
Gate-Source Charge	Q _{gs}		-	3.9	-	
Gate-Drain Charge	Q _{gd}		-	4.3	-	
Reverse Recovery Charge	Q _{rr}	I _F =-5A, di/dt=100A/us	-	140	-	ns
Reverse Recovery Time	t _{rr}		-	70	-	
Turn-on Delay Time	t _{D(on)}	V _{GS} =-10V, V _{DD} =-50V, R _L =2.5Ω R _{GEN} =6Ω	-	10	-	ns
Turn-on Rise Time	t _r		-	30	-	
Turn-off Delay Time	t _{D(off)}		-	77	-	
Turn-off fall Time	t _f		-	81	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_{DD}=-50V, V_G=-10V, R_G=25Ω, L=0.5mH, I_D=-12A.

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{θJA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



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Typical Electrical and Thermal Characteristics Diagrams

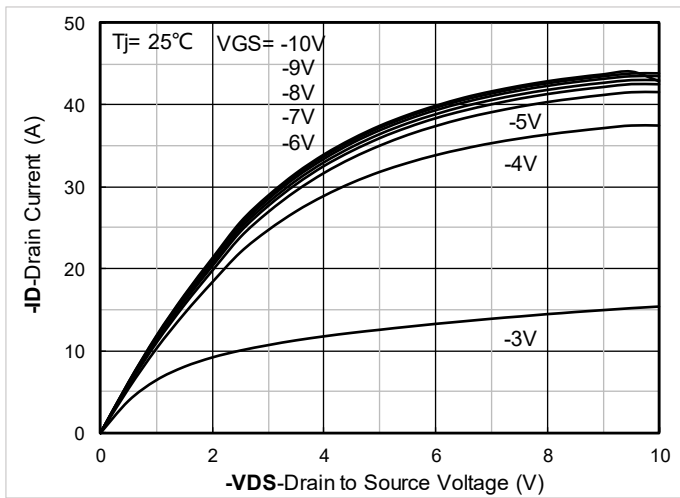


Figure1. Output Characteristics

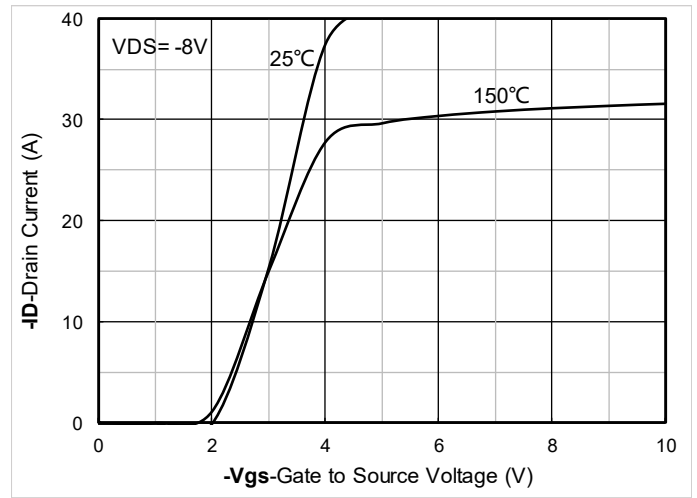


Figure2. Transfer Characteristics

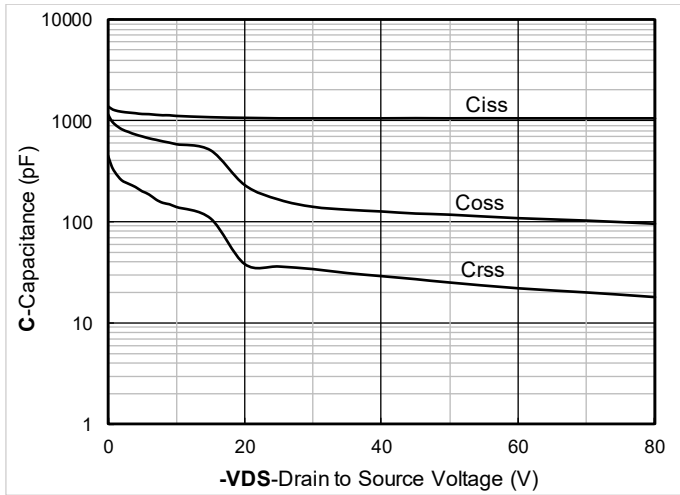


Figure3. Capacitance Characteristics

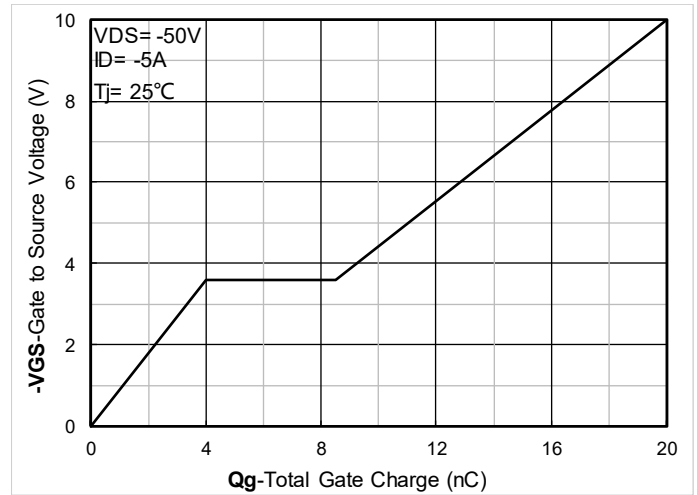


Figure4. Gate Charge

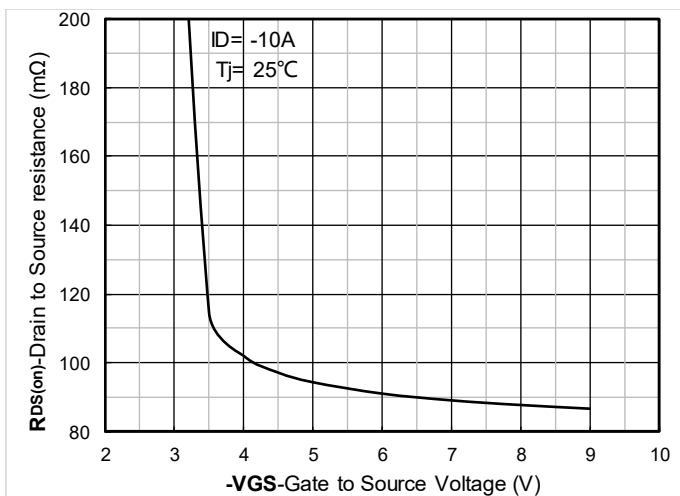


Figure5. On-Resistance vs Gate to Source Voltage

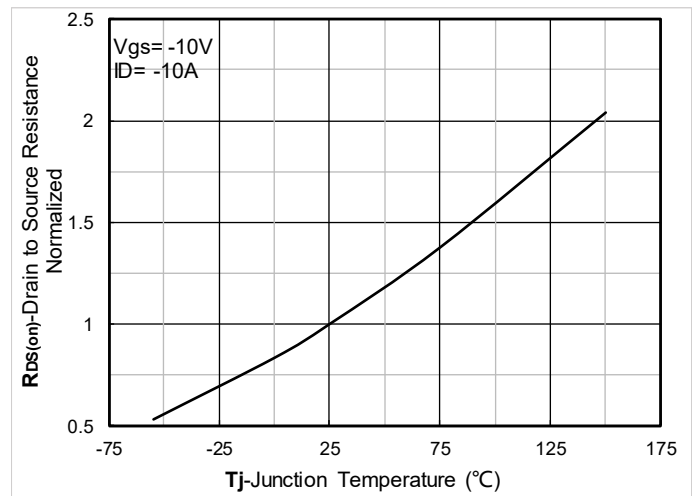


Figure6. Normalized On-Resistance



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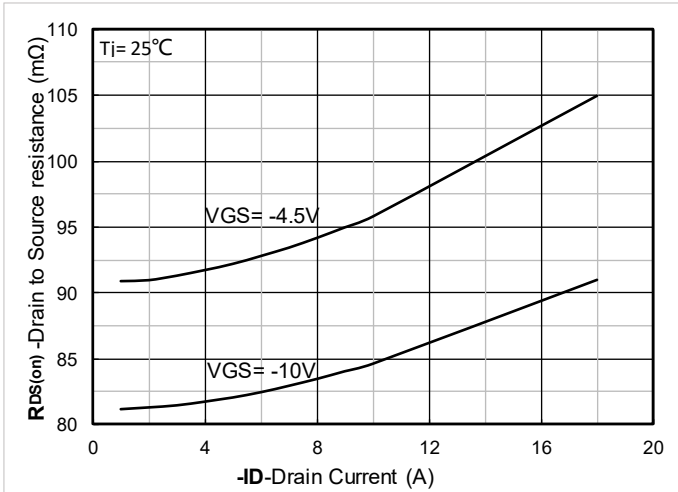


Figure7. RDS(on) VS Drain Current

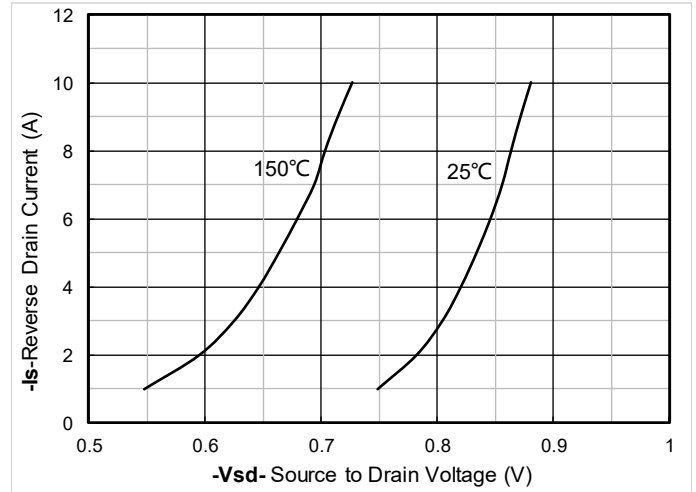


Figure8. Forward characteristics of reverse diode

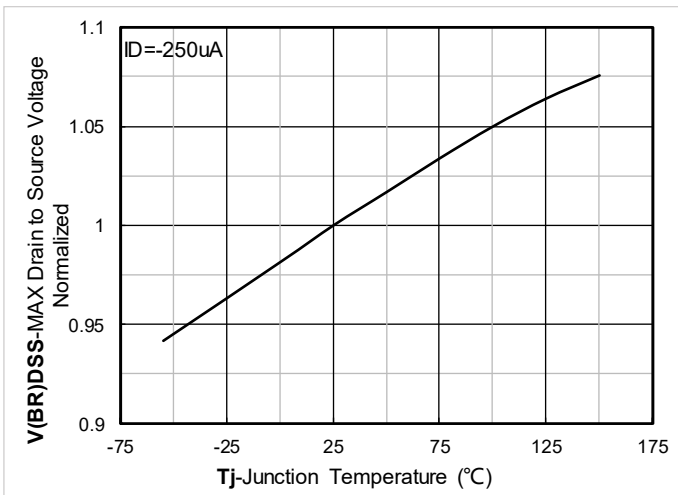


Figure9. Normalized breakdown voltage

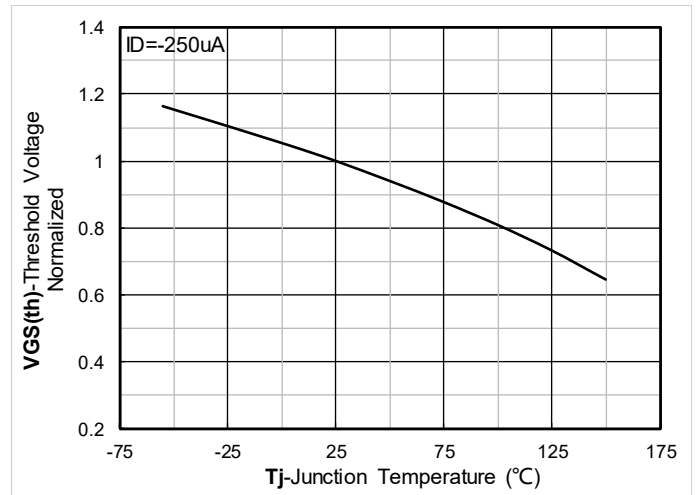


Figure10. Normalized Threshold voltage

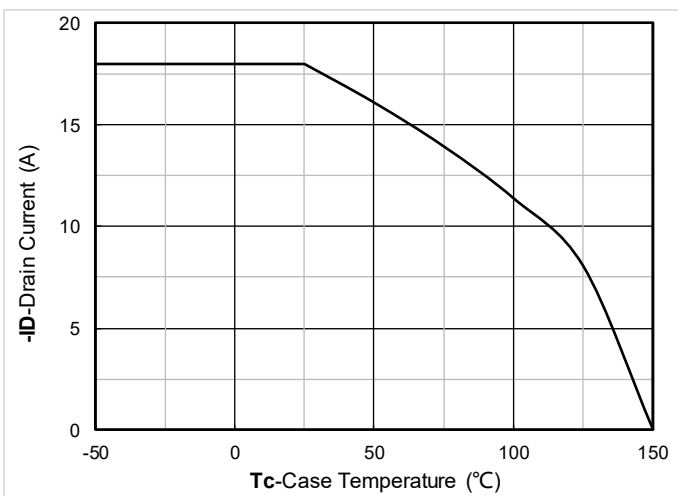


Figure11. Current dissipation

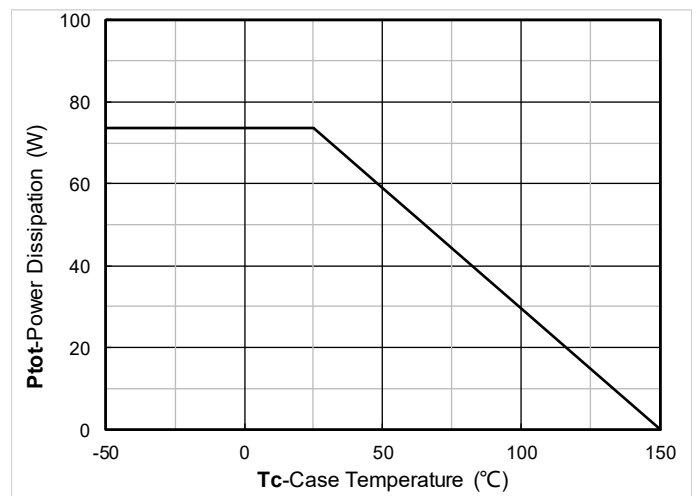


Figure12. Power dissipation



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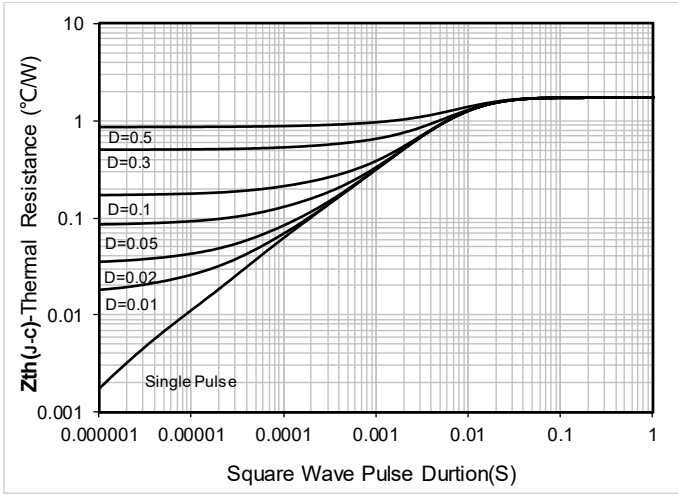


Figure13. Maximum Transient Thermal Impedance

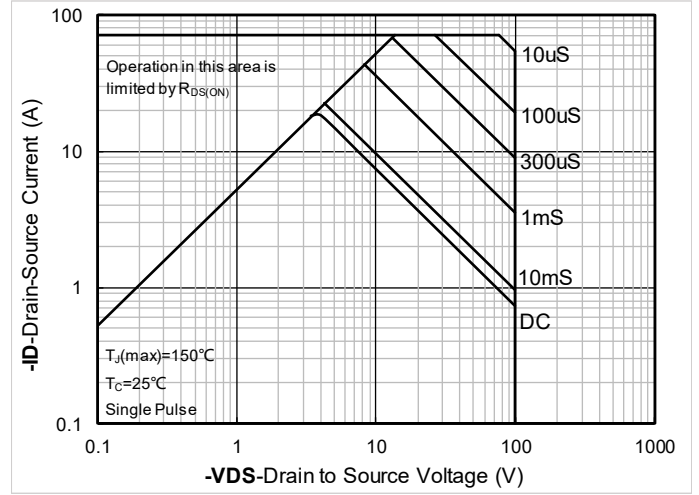
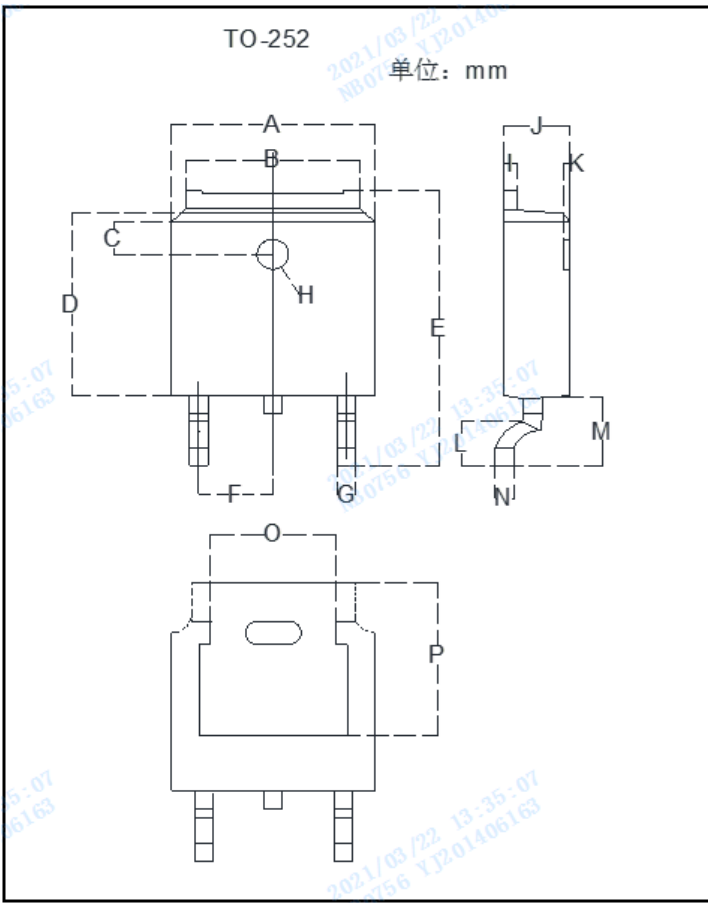


Figure14. Safe Operation Area



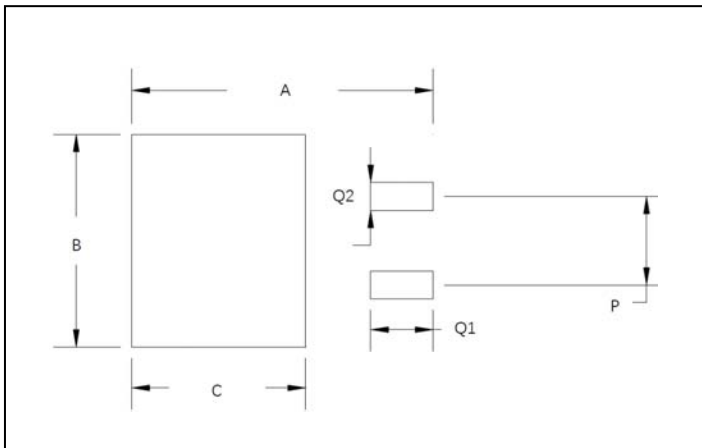
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■ TO-252 Package information



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.256	0.264	6.50	6.70	
B	0.201	0.215	5.10	5.46	
C	0.055	0.071	1.40	1.80	
D	0.236	0.244	6.00	6.20	
E	0.394	0.409	10.00	10.40	
F	0.085	0.093	2.17	2.37	
G	0.026	0.034	0.66	0.86	
H	Φ0.041	Φ0.531	Φ1.050	Φ1.350	
I	0.018	0.023	0.46	0.58	
J	0.087	0.094	2.20	2.40	
K	0.000	0.012	0.00	0.30	
L	0.035	0.090	0.89	2.29	
M	0.107	0.121	2.73	3.08	
N	0.017	0.023	0.43	0.58	
O	0.165	0.195	4.20	4.95	
P	0.203	0.215	5.15	5.45	

■ Suggested Pad Layout



Dim	Millimeters
A	11.4
B	6.74
C	6.23
P	4.56
Q1	2.28
Q2	1.52



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[PJMF600N65E1_T0_00201](#) [PJMF900N65E1_T0_00201](#) [PJMF900N60E1_T0_00201](#)